IN THE SPECIFICATION

Please amend the paragraph beginning on page 3, line 10, as follows:

-- Such a MRAM will be described more in detail. As illustrated in FIG. 14, a TMR element 10 which constitutes a memory ~~element~~ cell in a memory ~~cell~~ element of MRAM includes a memory layer 2 in which magnetization is relatively easily rotated, and magnetization pinned layers 4, 6, laminated on a support substrate 9.--

Please amend the paragraph beginning on page 14, line 4, as follows:

--FIGS. 1A to ~~2B~~ 1B is a cross-sectional view of a schematic diagram of an MRAM package according to a preferred embodiment of the present invention (FIG. 1A), and a plan view thereof more in specific (FIG. 1B).--

Please amend the paragraph beginning on page 15, line 29, as follows:

--FIG. 15 is a perspective view in schema of a ~~portion~~ plurality of a memory ~~cell unit~~ cells in an MRAM element.--

Please amend the paragraph beginning on page 18, line 28, as follows:

--Further, according to the preferred embodiments of the present invention, there are shown an exemplary case (FIGS. 1A and ~~2B~~ 1B) where magnetic shield layers 33, 34 having a saturation magnetization at 1.8 T or more are disposed on the top and the bottom surfaces of a sealing material 32 which encapsulates MRAM elements 30 having built-in TMR elements together with other elements such as DRAM or the like (DRAM 45, DSP 46 and RF 47 to be described later), another exemplary case (FIG. 2) where the magnetic shield layers 33, 34 are disposed, within the sealing material 32, on the upper portion of the MRAM element 30 and on the lower portion of the die pad 40, and still another exemplary case (FIG. 3) where they are embedded in a non-contacting state, respectively.--